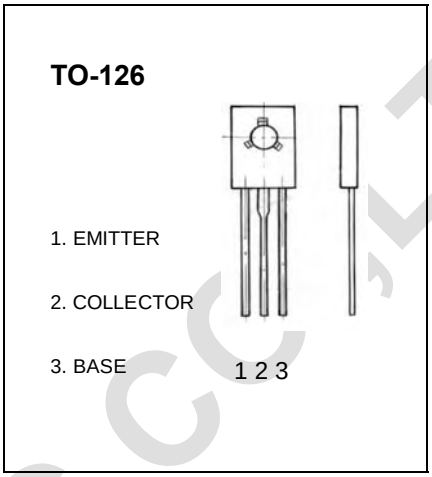
2SB1658 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM}: 1 W (Tamb=25℃)

Collector current

I_{CM}: -5 A

Collector-base voltage

$V_{(BR)CBO}$: -30 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-0.1mA, I_E=0	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-1mA, I_B=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.1mA, I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-30V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-2V, I_C=-1A	150		600	
	$h_{FE(2)}$	V_{CE}=-2V, I_C=-4A	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1A, I_B=-50mA I_C=-2A, I_B=-100mA I_C=-4A, I_B=-200mA			-0.15 -0.25 -0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-1A, I_B=-100mA			-1.5	V
Transition frequency	f_T	V_{CE}=-10V, I_C=-50mA		95		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		100		pF